REMARKS

Claims 1 and 8 are amended herein. Support for the amendments to the claims can be found in the specification on page 10, lines 3-7, 20-26 and Figures 1A and 1B. Upon entry of the amendment, claims 1-14 will be all the claims pending in the application.

I. Claim Rejections Under 35 U.S.C. § 103

Claims 1-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Okamoto et l (U.S. Patent No. 6,265,288) in combination with Li et al (U.S. Patent No. 5,772,771). This rejection is respectfully traversed.

The present invention is directed to a process of forming a film comprising (a) starting a supply of a reaction gas at a first flow rate such that an initial film is formed on a wafer and (b) starting a supply of the reaction gas at a second flow rate, after step (a), and while the supply of the reaction gas at said first flow rate continues, such that the film is formed on the initial film, and wherein the first flow rate is smaller than the second flow rate.

On the other hand, Okamoto et al discloses that the silane gas is provided with a flow rate of 1.1 to 1.5 times larger when the photoelectric conversion layer 205 has been completely deposited. Therefore, Okamoto et al do not teach or suggest the present process wherein a supply of the reaction gas is started at a second flow rate after an initial supply of a reaction gas at a first flow rate, while the supply of the reaction gas at said first flow rate continues, and wherein the first flow rate is smaller than the second flow rate.

Further, Okamoto et al do not teach or suggest that the first flow rate and the second flow rate are applied to different lines, respectively. In the present invention, as shown in Figures IA, B and 3, the flow timings and the flow rates for different lines are controlled.

Li does not remedy the deficiencies of Okamoto et al.

In view of the above, one of ordinary skill in the art would not have had a reasonable expectation of achieving the claimed invention based upon the disclosure of Okamoto et al and Li, alone or in combination. Accordingly Applicants respectfully request withdrawal of the rejection.

II. Conclusion

In view of the above, reconsideration and allowance of this application are now believed to be in order, and such actions are hereby solicited. If any points remain in issue which the Examiner feels may be best resolved through a personal or telephone interview, the Examiner is kindly requested to contact the undersigned at the telephone number listed below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

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APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

1. (Amended) A method of forming a film, comprising the steps of:

(a) starting a supply of a reaction gas at a first flow rate into a chamber in which a plasma is formed, such that an initial film is formed on a wafer; and

(b) starting a supply of the reaction gas at a second flow rate into the chamber in which the plasma is formed, after said step (a), while the supply of the reaction gas at said first flow rate continues such that the film is formed on the initial film, the first flow rate being smaller than the second flow rate.

8. (Amended) A method of forming a film, comprising the steps of:

(a) forming a film from a center region of a wafer by supplying a reaction gas at a first flow rate, while a thickness of the film is equal to or thinner than 10 nm; and

(b) forming the film on ~~whole of~~ said wafer, by ~~supplying~~ starting to supply the reaction gas at a second flow rate, after said step (a), while continuing to supply the reaction gas at said first flow rate.

9. (Amended) The method according to claim 8, wherein ~~said step (a) comprises the step of:~~

~~supplying said reaction gas at a first flow rate,~~

~~said step (b) comprises the step of:~~

~~supplying said reaction gas at a second flow rate, and~~

said first flow rate is in a range of one fifth to one tenth of said second flow rate.